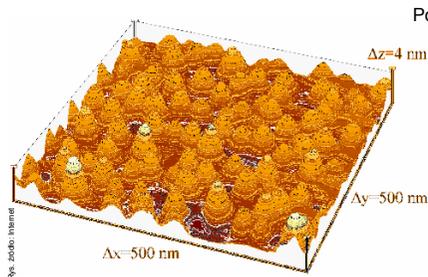


## Nanotechnologie (II)

Jacek.Szczytko@fuw.edu.pl <http://www.fuw.edu.pl/~szczytko>



Półprzewodniki

a.Studnie

- i.Studnie i ekscytyny
- ii.Lasery
- iii.Dwuwymiarowe gazy

b.Druty

- i.Półprzewodniki
- ii.Organika
- iii.Laser z drutów

c.Kropki

- i.Kropki planowane i nie
- ii.Tranzystor na pojedynczym elektronie

## Jeszcze o teoriach (nie tylko fizycznych)

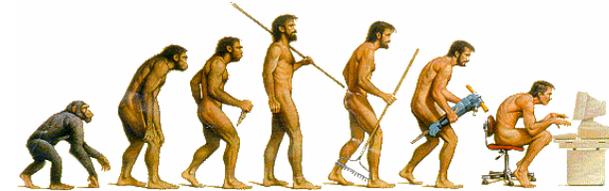
**Odpowiedzialność za słowo** – pojęcia mają znaczenie (energia, fale, polaryzacja, moderator pola, stężenie w roztworze) i dają się przekazać drugiej osobie bez uciekania się do przenośni.

**Uczciwość** – doświadczenie jest arbitrem.

**Teoria naukowa** jest naukowa gdy:

- Jest testowalna
- Jest falsyfikowalna
- Przewiduje wyniki

[Karl Popper + dyskusje (e.g. Thomas Kuhn)]



## Jeszcze o teoriach (nie tylko fizycznych)

POPPER, Karl, 1980. Evolution. [New Scientist](#) 87(1215):611.

In the 17 July issue of *New Scientist* (p. 215) you published an article under the title „Popper: good philosophy, bad science?” by Dr Beverly Halstead. This article, it appears had two purposes:

1. To defend the scientific character of the theory of evolution, and of palaeontology. I fully support this purpose, and this letter will be almost exclusively devoted to the defence of the theory of evolution.
2. To attack me.

As to (2). I find this uninteresting and I shall not waste your space and my time in defending myself against what are in my opinion hardly excusable misunderstandings and wild speculations about my motives and their alleged history.

Returning to (1), it does appear from your article (provided its quotation from Colin Patterson's book – which I do not know – is not as misleading as your quotations from my book) that some people think that I have denied scientific character to the historical sciences, such as palaeontology, or the history of the evolution of life on Earth; or to say, the history of literature, or of technology, or of science.

This is a mistake, and I here wish to affirm that these and other historical sciences have in my opinion scientific character: their hypotheses can in many cases be **tested**.

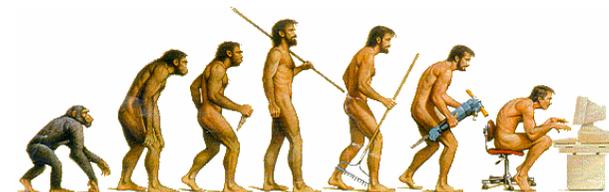
It appears as if some people would think that the historical sciences are untestable because they describe unique events. However, **the description of unique events can very often be tested by deriving from them testable predictions or retrodictions.**

## Jeszcze o teoriach (nie tylko fizycznych)

# Pytać!

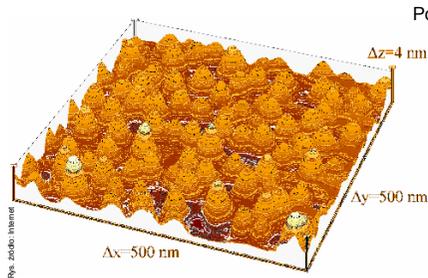
Jeżeli jakaś teoria filozoficzna nie daje się przetłumaczyć na góralski, to jest to teoria fałszywa.

Józef Tischner



## Nanotechnologie (II)

Jacek.Szczytko@fuw.edu.pl <http://www.fuw.edu.pl/~szczytko>



Półprzewodniki

a. Studnie

- i. Studnie i ekscytony
- ii. Lasery
- iii. Dwuwymiarowe gazy

b. Druty

- i. Półprzewodniki
- ii. Organika
- iii. Laser z drutów

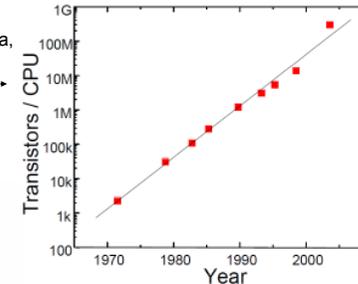
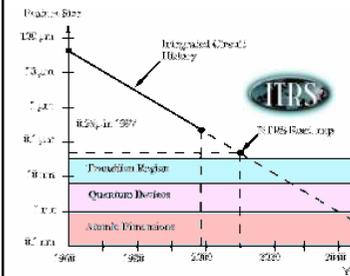
c. Kropki

- i. Kropki planowane i nie
- ii. Tranzystor na pojedynczym elektronie

## TRENDY: Pierwsze Prawo Moore'a

Ilość komponentów ( tranzystory, połączenia, izolacje itd.) w IC podwaja się co około 18 miesięcy.

Rozmiar liniowy komponentów również zmniejsza się wykładniczo w czasie.



Te trendy nie mogą być kontynuowane w nieskończoność.

- Co zastąpi technologię Si?
- Z czego będzie wynikała ta zmiana technologii?

**EKONOMIA**

Źródło: Intel

## Nanotechnologie

### JAK?

- Top-down, czyli (nano)technologia
- Bottom-up, czyli samoorganizacja

### CO?

- Studnie, druty, kropki
- Nanorurki i nanomaszyny

↓ Top-down

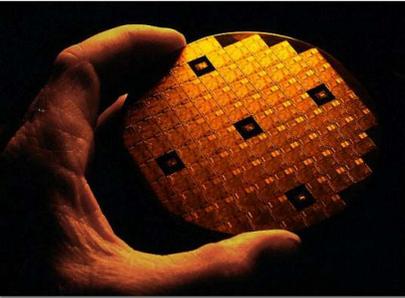


Vincent Laforet/The New York Times

Jacek Szczętko@fuw.edu.pl http://www.fuw.edu.pl/~szczytko

## Top-down, czyli małe jest piękne!

Nanotechnologia  
Litografia  
Udoskonalenia  
Galeria  
Fizyka na Hożej



Prescot, Intel



## ↑ Bottom-up

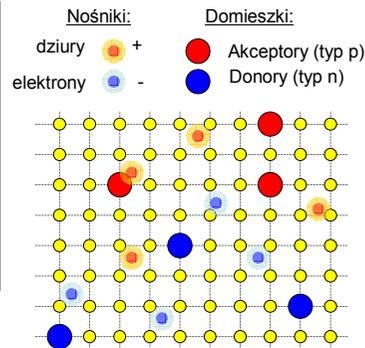


© Stuart McKim

## Półprzewodniki

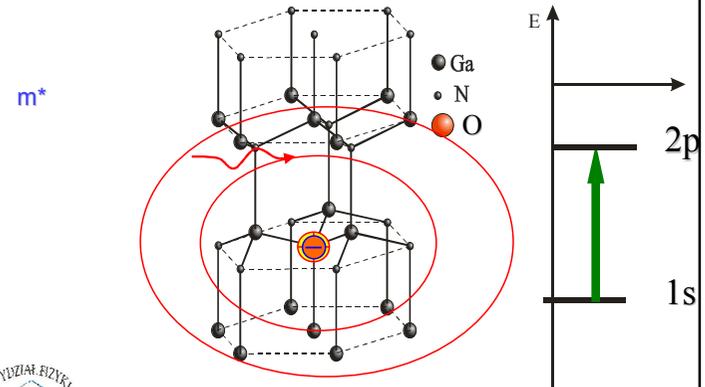
II	III	IV	V	VI
Be	B	C	N	O
Mg	Al	Si	P	S
Zn	Ga	Ge	As	Se
Cd	In	Sn	Sb	Te

**Grupa IV:** diament, Si, Ge  
**Grupy III-V:** GaAs, AlAs, InSb, InAs...  
**Grupy II-VI:** ZnSe, CdTe, ZnO, SdS...

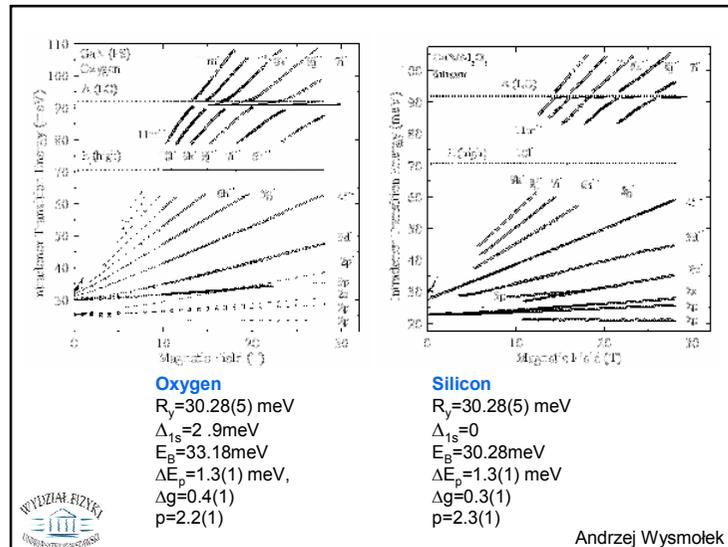
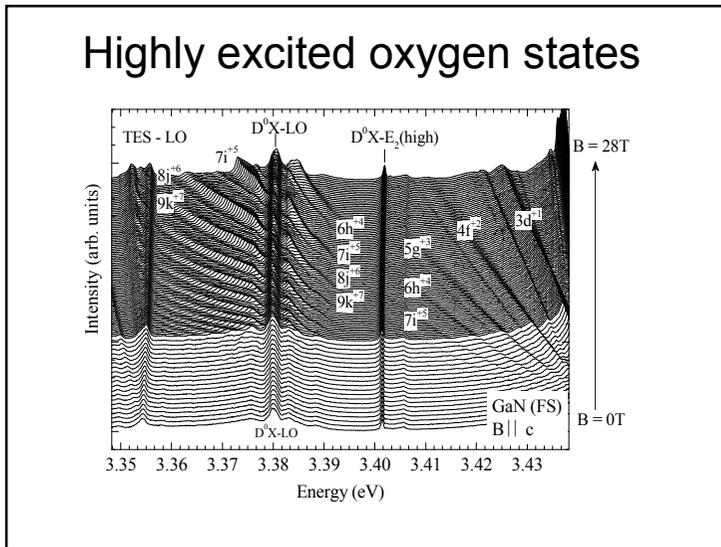
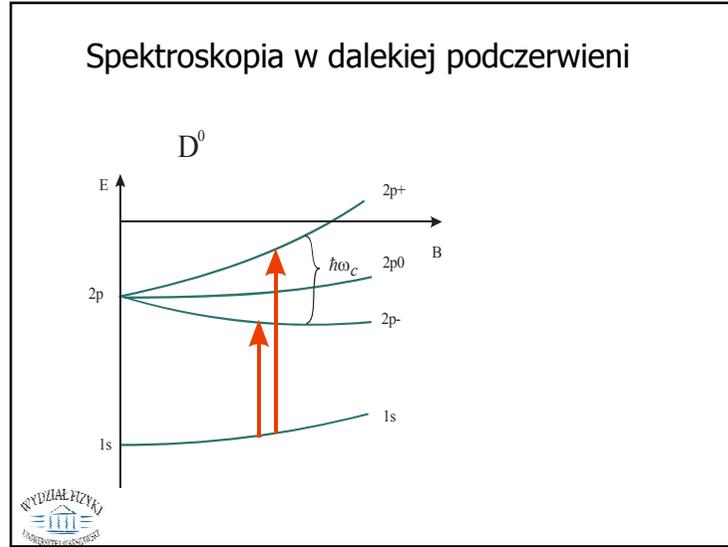
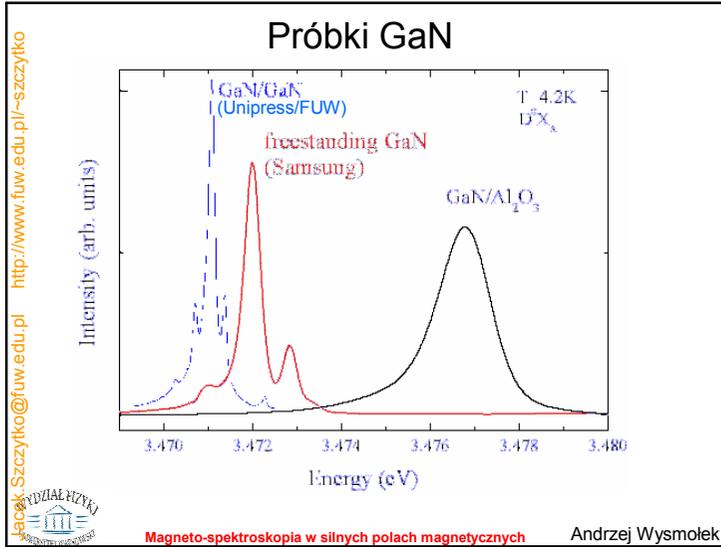


## Neutralny donor

Magneto-spektroskopia w silnych polach magnetycznych



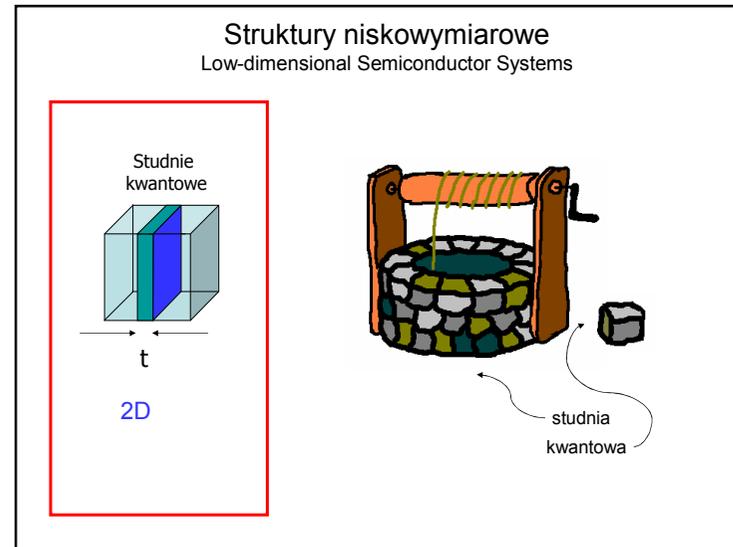
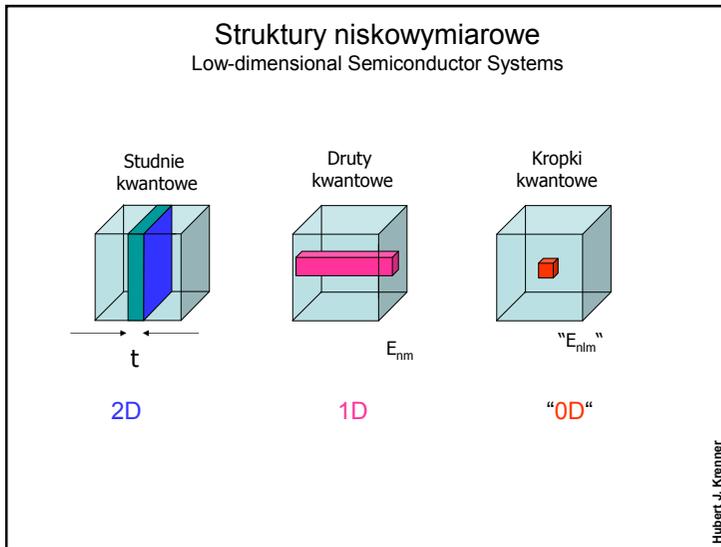
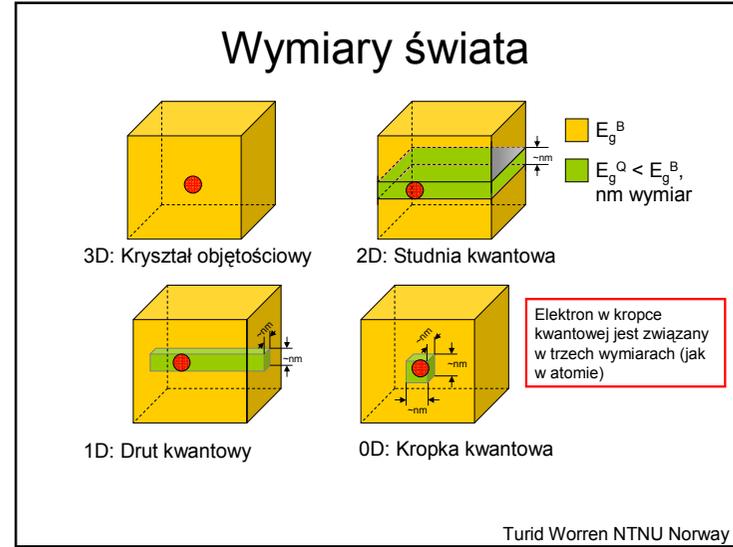
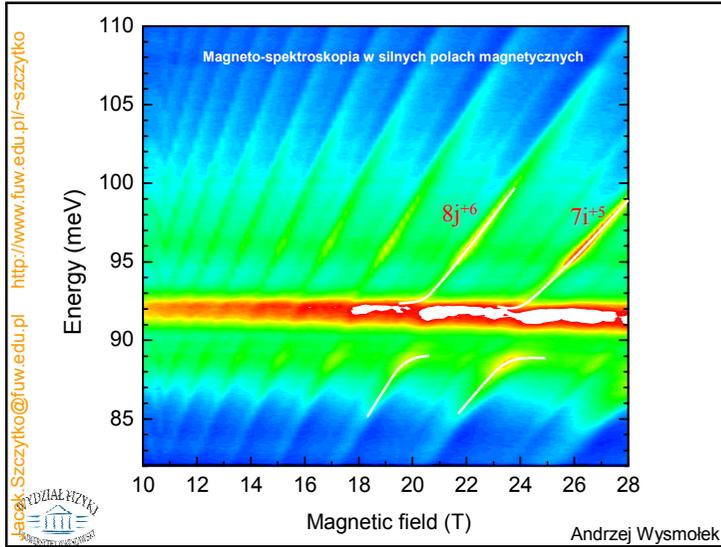
Andrzej Wymorek



**Oxygen**  
 $R_y = 30.28(5) \text{ meV}$   
 $\Delta E_s = 2.9 \text{ meV}$   
 $E_B = 33.18 \text{ meV}$   
 $\Delta E_p = 1.3(1) \text{ meV}$   
 $\Delta g = 0.4(1)$   
 $p = 2.2(1)$

**Silicon**  
 $R_y = 30.28(5) \text{ meV}$   
 $\Delta E_s = 0$   
 $E_B = 30.28 \text{ meV}$   
 $\Delta E_p = 1.3(1) \text{ meV}$   
 $\Delta g = 0.3(1)$   
 $p = 2.3(1)$

Andrzej Wyszomlek



Prof. Andrzej Twardowski

## Cząstka w studni potencjału

Warunek  $kL = n\pi \Rightarrow k = n\frac{\pi}{L} \quad n = 1, 2, 3, \dots$

oznacza, że wektor falowy może przyjmować tylko niektóre wartości, czyli że jest **skwantowany**

Podobnie energie są **skwantowane**:

$$E = \frac{\hbar^2 k^2}{2m} = \left( \frac{\hbar^2 \pi^2}{2mL^2} \right) n^2$$

„klasyczna” cząstka w studni mogłaby mieć dowolne energie i przebywać w dowolnym miejscu studni.

Prawdopodobieństwo (kwadrat funkcji falowej)

Prof. Andrzej Twardowski

## Cząstka w studni skończonej

W przypadku studni skończonej też jest kwantyzacja energii (ale są też energie nieskwantowane).

Funkcja falowa rozciąga się poza barierę!

Cząstka może wnikać w barierę!

Zasadnicza różnica: Klasyczna cząstka nie może wnikać w barierę.

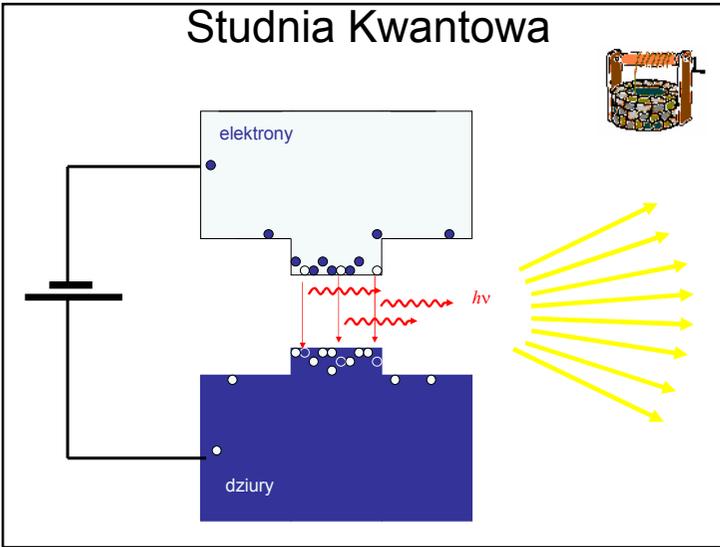
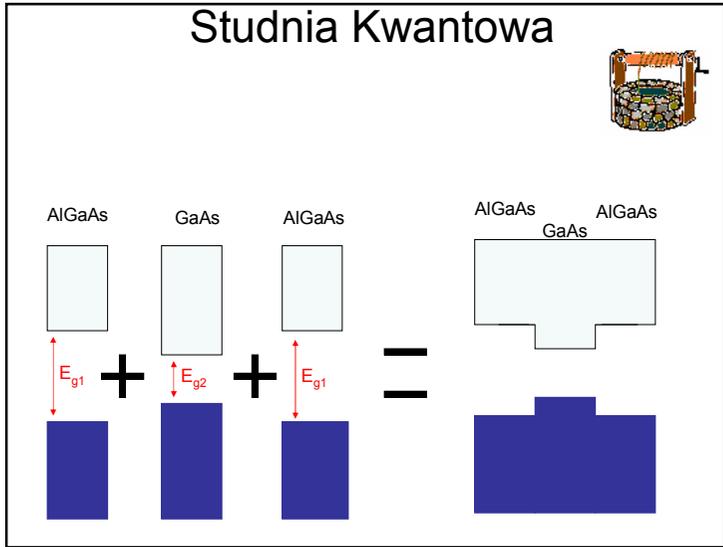
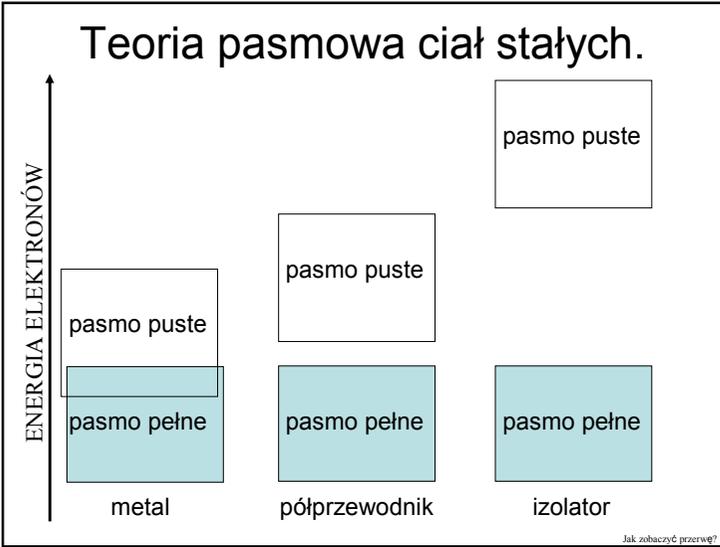
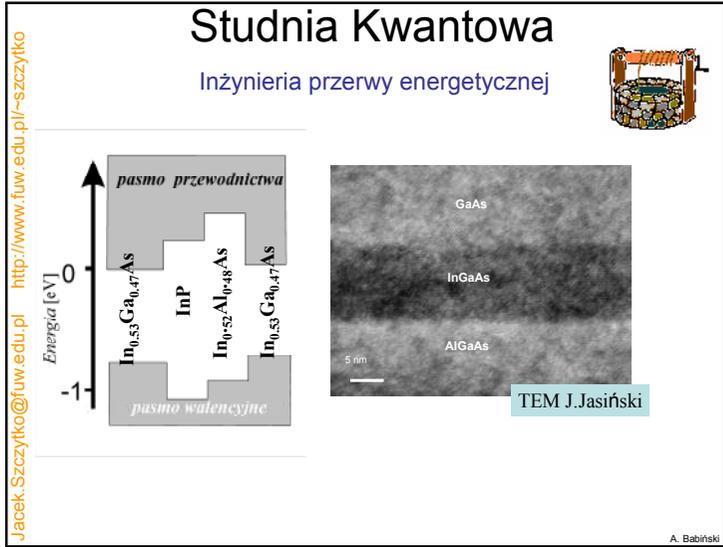
## MBE

MBE → Osadzanie z atomową precyzją warstw o różnym składzie lub domieszkowaniu

Hubert J. Krenner

## MOCVD

MOCVD → Osadzanie z atomową precyzją warstw o różnym składzie lub domieszkowaniu



# Studnie Kwantowe

Lasery półprzewodnikowe

The diagram shows a laser structure with an emitting region and a top metallic contact. The layers from top to bottom are: Top Metallic Contact, Proton Bombarded Semi-Insulating Barrier, p+ GaAs, p AlGaAs, Active Region, n AlGaAs, n GaAs Substrate, and Bottom Contact. The emitting region is shown as a quantum well structure.

<http://www.fuw.edu.pl/~szczytko>

## Vertical Cavity Surface Emitting Laser

The diagrams illustrate four VCSEL structures:

- Metalic Reflector VCSEL:** Features an n-InP substrate, n-InP Active Region, p-InP, and SiO<sub>2</sub>. It uses an Au/Zn circular mirror and electrode. Light out is shown from the top.
- Etched Well VCSEL:** Features a p-n-p-n structure with an Active Region and n-substrate. It uses a Dielectric Mirror. Light out is shown from the bottom.
- Air Post VCSEL:** Features an Au/Ti Contact, Active Region, p DBR, n DBR, and substrate. Light out is shown from the bottom.
- Burried Regrowth VCSEL:** Features an Au/Ti Contact, Epitaxial Regrowth, p DBR, Active Region, n DBR, and substrate. Light out is shown from the bottom.

<http://brimneyspear.ac.phy.stcs.vcsels.htm>

# QCL - Quantum Cascade Laser

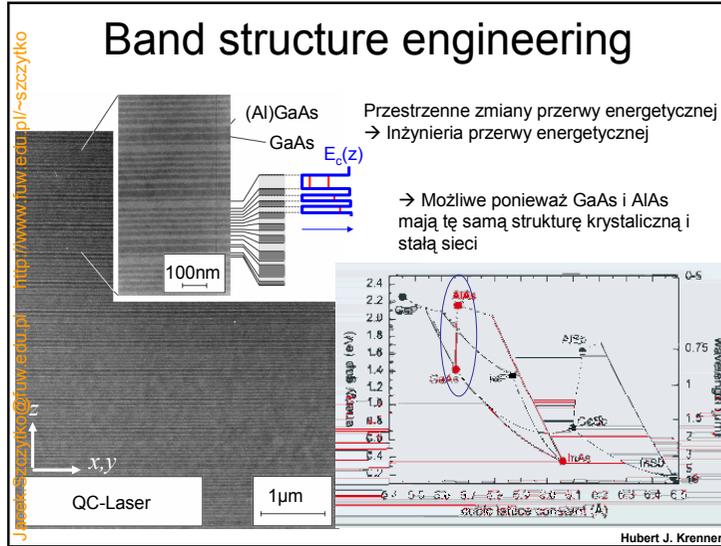
The diagram shows a schematic of a QCL structure with multiple stages of quantum wells. Electrons are shown cascading through the wells, emitting photons at each stage.

# QCL - Quantum Cascade Laser

The schematic shows the energy levels of a QCL structure, including AlAs, Al<sub>0.45</sub>In<sub>0.55</sub>As, Ga<sub>0.45</sub>In<sub>0.55</sub>As, and InAs layers, with minibands and minigaps. Below are photographs of QCL components:

- The QUANTA® OEM module (LASER COMPONENTS)
- A photograph of a QCL laser head with a handwritten signature.

[http://www.sacher-laser.com/QCL\\_LaserHead.php](http://www.sacher-laser.com/QCL_LaserHead.php)

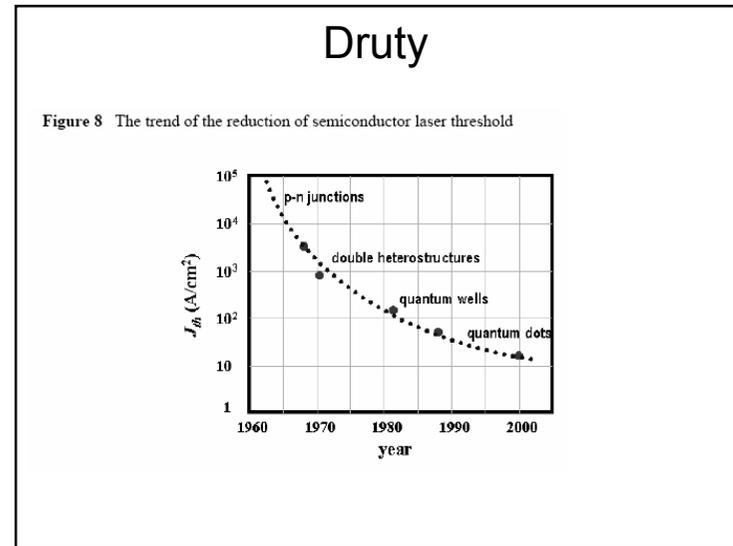
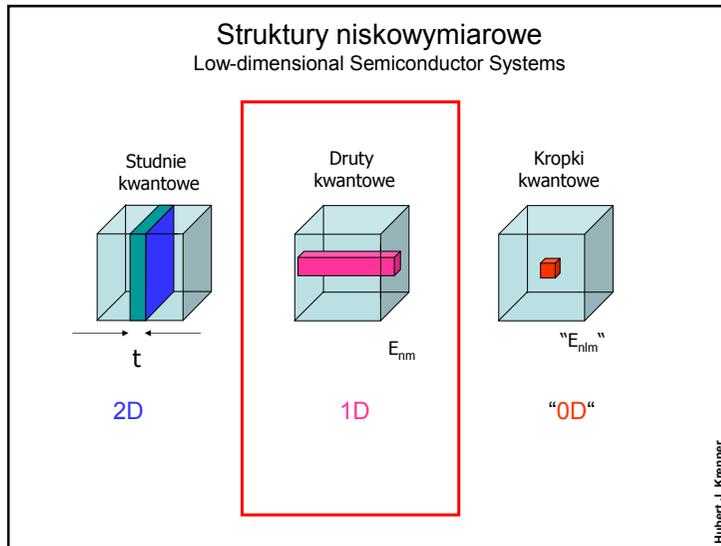


## Studnie Kwantowe

Więcej: <http://britneyspears.ac/lasers.htm>

Conduction Band

Valence Band



**Druty**

PHYSICAL REVIEW B VOLUME 52, NUMBER 15 15 OCTOBER 1995-1

**Dimensionality effects on strain and quantum confinement in lattice-mismatched InAs, P<sub>1-x</sub>/InP quantum wires**

M. Notomi\*  
NTT Opto-electronics Laboratories, 3-1 Morinosato-Wakamiya, Atsugi, Kanagawa 243-02, Japan

J. Hammersberg and H. Weman  
Department of Physics and Measurement Technology, Linköping University, S-581 83 Linköping, Sweden

S. Nojima, H. Sugiura, M. Okamoto, and T. Tamamura  
NTT Opto-electronics Laboratories, 3-1 Morinosato-Wakamiya, Atsugi, Ka

M. Potemski  
Grenoble High Magnetic Field Laboratory, Max-Planck Institute für F and Centre National de la Recherche Scientifique, 38042 Greno  
(Received 29 March 1995)

(a) CBE Growth (b) EB Writing (c) Cap Etching (d) Reverse-mesa Etching (e) Wire Formation (f) Overgrowth

FIG. 1. Fabrication process of strained InAsP/InP quantum wires.

**Druty**

Figure 11 Growth of quantum wires on a vicinal surface with multiatomic steps

(a) (b)

buffer (AlAs/GaAs) substrate (GaAs) quantum wire

Figure 12 Selective growth of quantum wires on a pre-patterned V-groove substrate

(a) (b)

barrier (AlGaAs) substrate (GaAs) quantum wire

**Druty**

Figure 9 Quantum wire fabrication based on nanoscale etching and re-growth

(a) etching (b) re-growth

buffer substrate quantum wire

Figure 10 Formation of one-dimensional nanoscale quantum wires by strain-induced lateral ordering

(a) (b)

buffer (InGaAs) substrate (InP) quantum wire array

**Druty**

Figure 13 Selective growth of quantum wires on a pre-patterned  $\Lambda$ -ridge substrate

(a) (b)

barrier (AlAs) substrate (GaAs) quantum wire

Figure 14 Formation of one-dimensional T-intersection quantum wire structure by cleaved-edge overgrowth

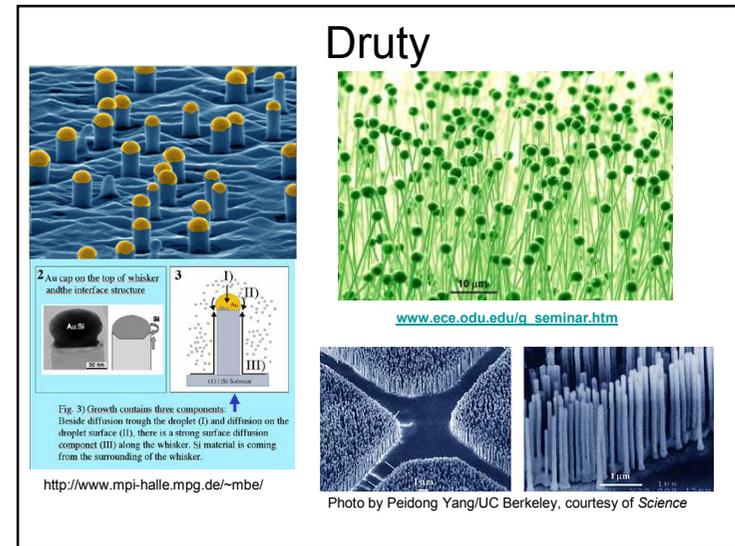
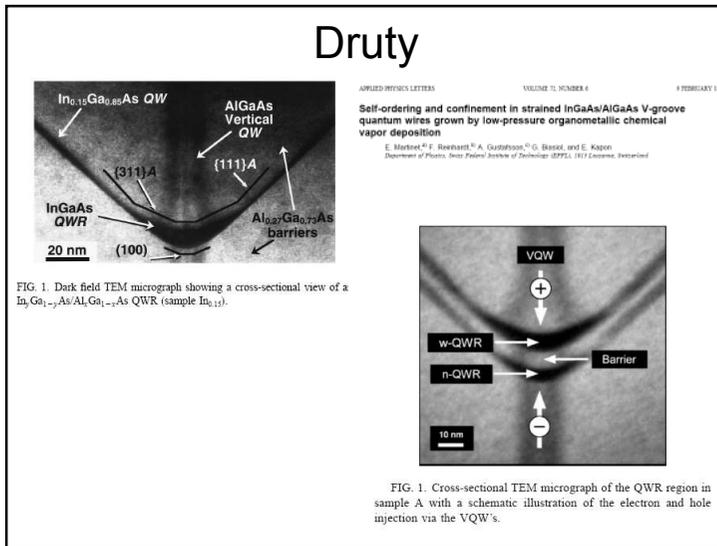
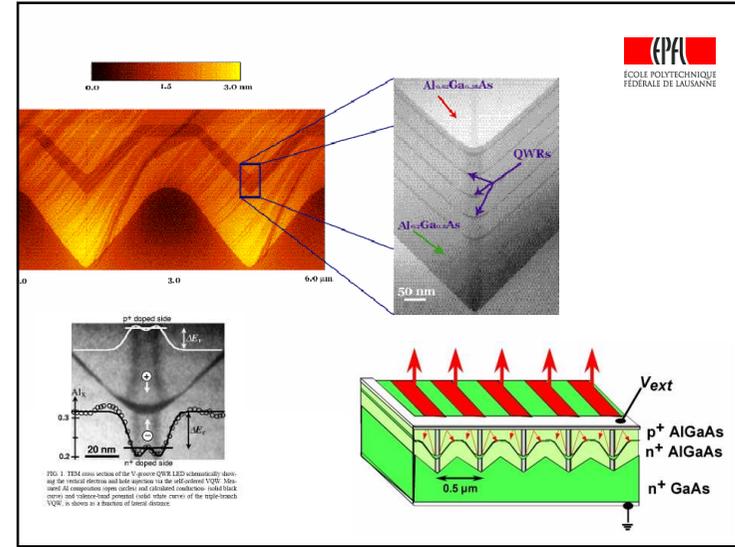
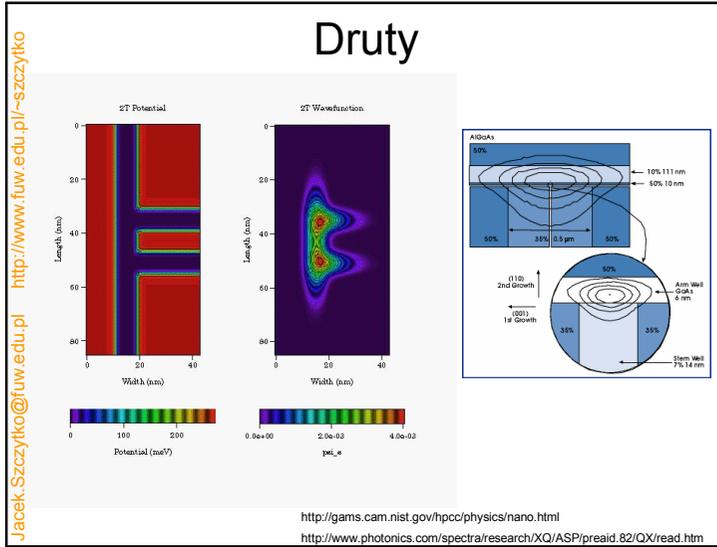
(a) (b) (c)

quantum well cleavage overgrowth

substrate (GaAs) quantum wire

42 Int. J. of Nanotechnology, Vol. 1, No. 1/2, 2004  
Nanolasers: Lasing from nanoscale quantum wires  
Samuel S. Mao

42 Int. J. of Nanotechnology, Vol. 1, No. 1/2, 2004  
Nanolasers: Lasing from nanoscale quantum wires  
Samuel S. Mao



# Druty

P.X. Gao et al. / Chemical Physics Letters 408 (2005) 174-178

175

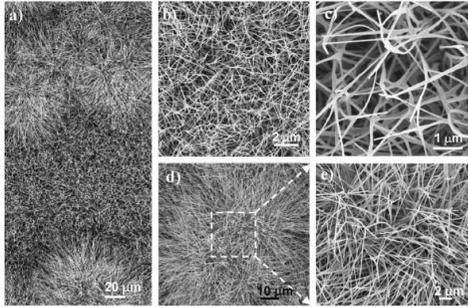


Fig. 1. (a) A typical low magnification SEM image of the as-grown networks of ZnO nanowires and nanorods consisting two o types of morphologies, as indicated by area b (b,c) and c (d,e). (b,c) Enlarged SEM images of uniform networks of ZnO nanowires and nanorods. (d,e) Enlarged SEM images of clumps of nanowires showing the interconnected nanowires and nanorods.

# Druty

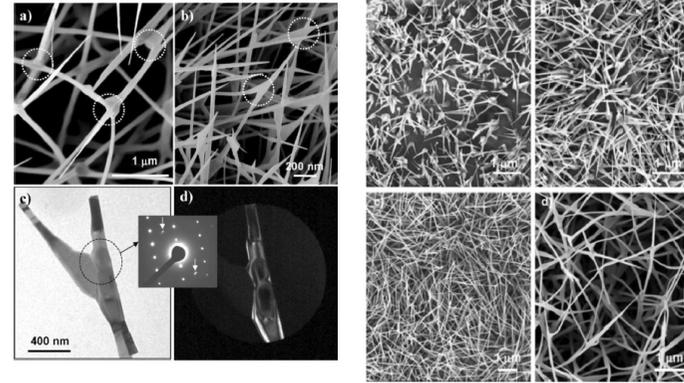


Fig. 3. The morphology of ZnO nanowires. (a) The typical image of interconnected nanowires and nanorods. (b) The typical image of interconnected nanowires and nanorods. (c) The typical image of interconnected nanowires and nanorods. (d) The typical image of interconnected nanowires and nanorods. (e) The typical image of interconnected nanowires and nanorods. (f) The typical image of interconnected nanowires and nanorods. (g) The typical image of interconnected nanowires and nanorods. (h) The typical image of interconnected nanowires and nanorods. (i) The typical image of interconnected nanowires and nanorods. (j) The typical image of interconnected nanowires and nanorods.

Fig. 4. (a,b) Interconnection types of ZnO nanowires in the nano-network. (c,d) Bright-field and dark-field TEM images of two nanowires interconnected with each other, indicating that the two nanowires are single crystals but they have no orientational relationship. The circle area is used for recording the selected area electron diffraction pattern (inset).

# Druty

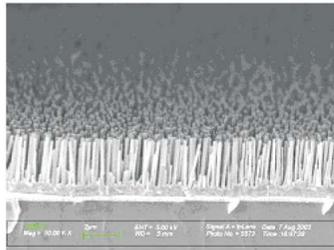


Figure 3. Si/SiO<sub>2</sub>/Ti/Pt/ZnO Nanowire.

Tamkang Journal of Science and Engineering, Vol. 7, No 3, pp. 135-138 (2004)

135

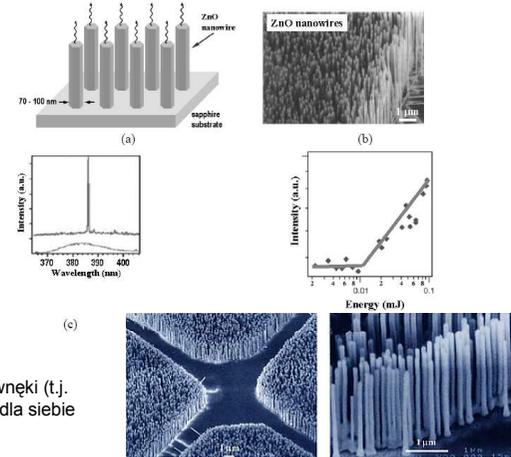
## Growth and Patterning of ZnO Nanowires on Silicon and LiNbO<sub>3</sub> Substrates

T. K. Shing\*, H. H. Pan, L-C Chen and C. I. Kuo

# Druty

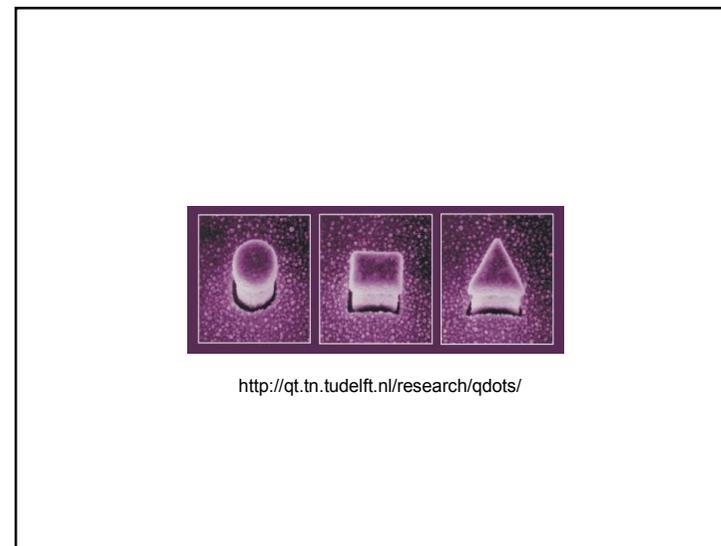
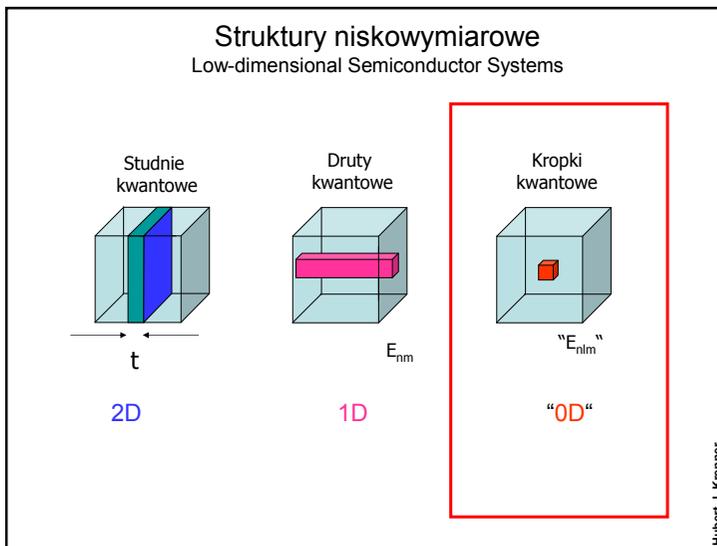
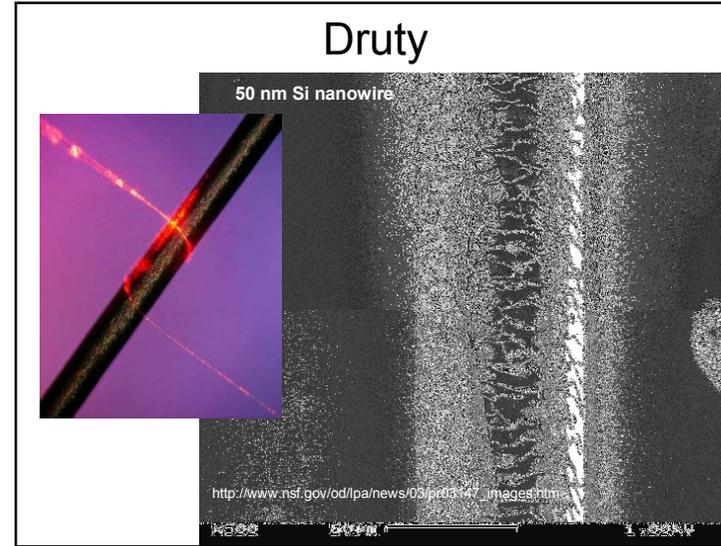
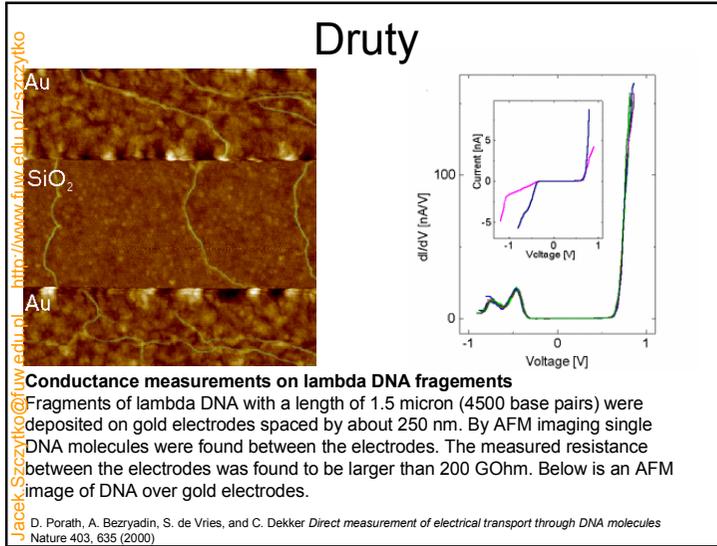
42 Jpn. J. of Nanotechnology, Vol. 1, No. 1/2, 2004  
Nanolasers: Lasing from nanoscale quantum wires

Samuel S. Mao



Laserowanie bez wnęki (t.j. sam nanodrut jest dla siebie wnęką!)

Photo by Peidong Yang/UC Berkeley, courtesy of Science



## Kropki

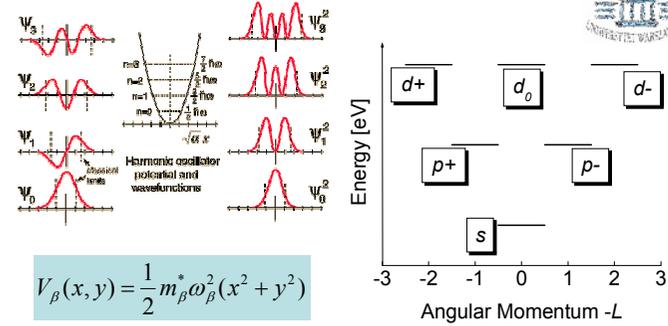
- Co to są Kropki Kwantowe - Quantum Dots (QD)
- W jaki sposób je się wytwarza
  - Nanotechnologia
  - Samoorganizujące się Kropki Kwantowe (Self-assembled Quantum Dots)

Textbook:

Mesoscopic region in a semiconductor surrounded by higher band gap material

- Pełna kwantyzacja stanów
- gęstość stanów funkcji  $\delta$  Diraca
- Wąskie widma spektralne w emisji i absorpcji
- „Sztuczne atomy” - “Artificial Atoms”

## Kropki kwantowe - lokalizacja w płaszczyźnie wzrostu



$$V_{\beta}(x, y) = \frac{1}{2} m_{\beta}^* \omega_{\beta}^2 (x^2 + y^2)$$

gdzie,  $\beta = e, h$

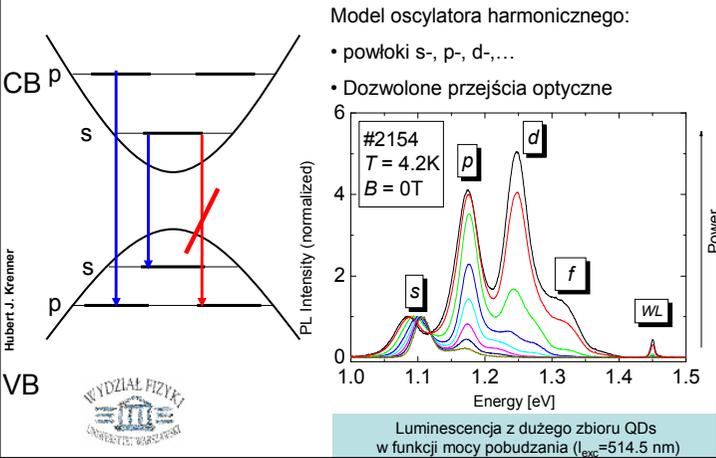
$$E_{\beta, n, m} = \hbar \omega_{\beta} (n + \frac{1}{2}) + \hbar \omega_{\beta} (m + \frac{1}{2})$$

$$n, m = 0, 1, 2, \dots$$

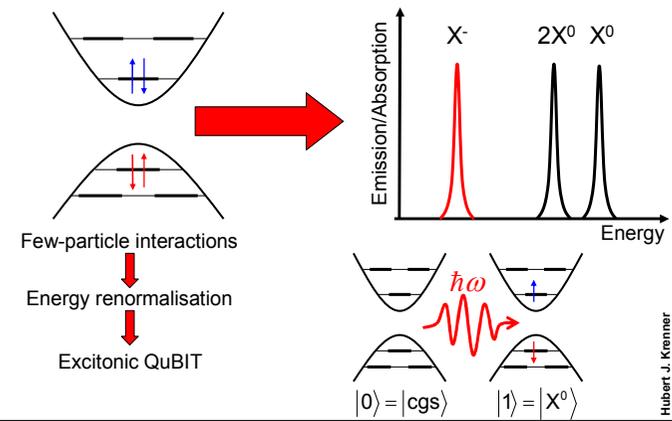
$$L = n - m \text{ (elektron)}$$

Adam Babiński

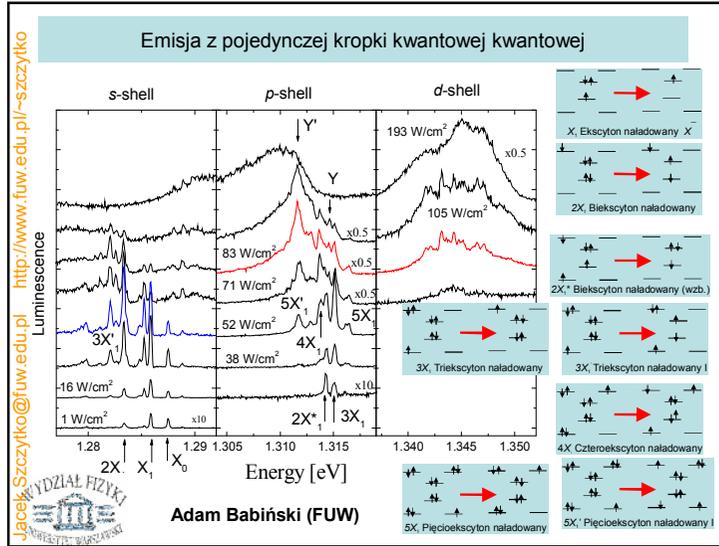
## Kropki kwantowe – sztuczne atomy



## Oddziaływania wielociałowe



Hubert J. Krenner



### Rodzaje kropek kwantowych

**"Klasyczne" kropki kwantowe**

**Specjalne techniki wzrostu**

**"Egzotyczne" Kropki kwantowe**

Hubert J. Kenner

### Electrostatically defined Quantum Dots

Two-dimensional electron system

Depletion by gate electrodes

Quantum Dots: Attractive confinement for electrons

Hubert J. Kenner

### Blokada Kulombowska

http://people.ccmr.cornell.edu/~ralph/projects/metalset/

Jacek.Szczytko@fuw.edu.pl http://www.fuw.edu.pl/~szczytko

## Kropki

**Silicon Single Electron Transistor**  
(After Gate Oxidation)

032803 5.0k X200k 150nm

**Silicon Single Electron MOS Memory**  
(Before Oxidation)

071507 4.0k X150k 200nm

NanoStructure Lab  
UNIVERSITY OF MINNESOTA

## Kropki

A series of superconducting aluminum disks (0.1 to 2 microns in size) sit on top of a semiconducting structure. Buried beneath the spots where the strips cross are tiny realms in which electrons, constituting 2-dimensional electron gases (2DEG), are sensitive to the magnetization of the disks above. In this way the size-dependent properties of superconductors no bigger than a Cooper pair (the electron doublets that form inside superconductors) can be studied.

## Positioning Quantum Dots – Patterned Substrate

Zhong *et al.*, APL **84**, 1922 (2004)

**Lithographically defined Diffusion**

**MBE defined Diffusion or Strain**  
Jochen Bauer

AlGaAs superlattice  
InGaAs layers

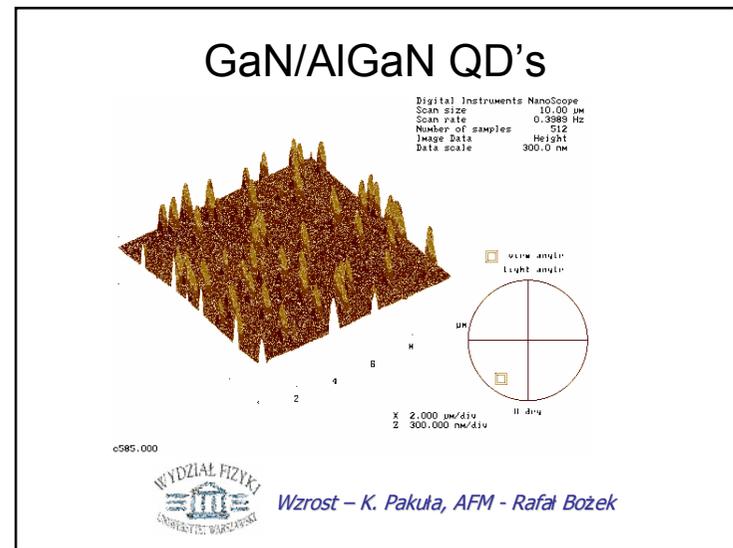
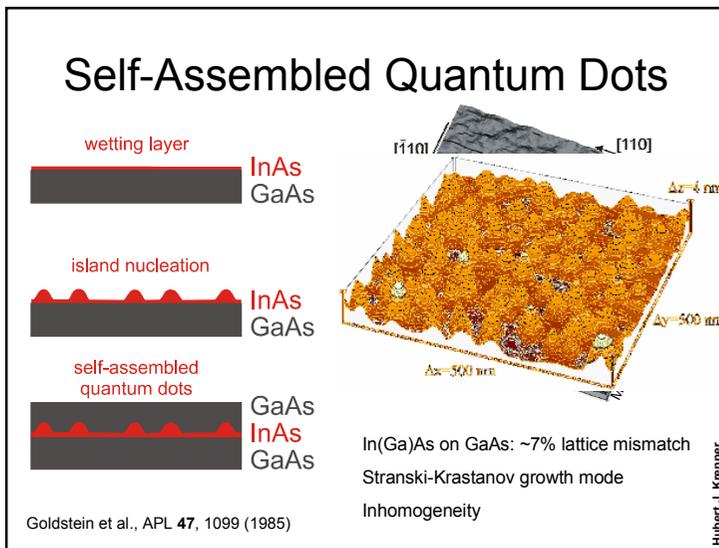
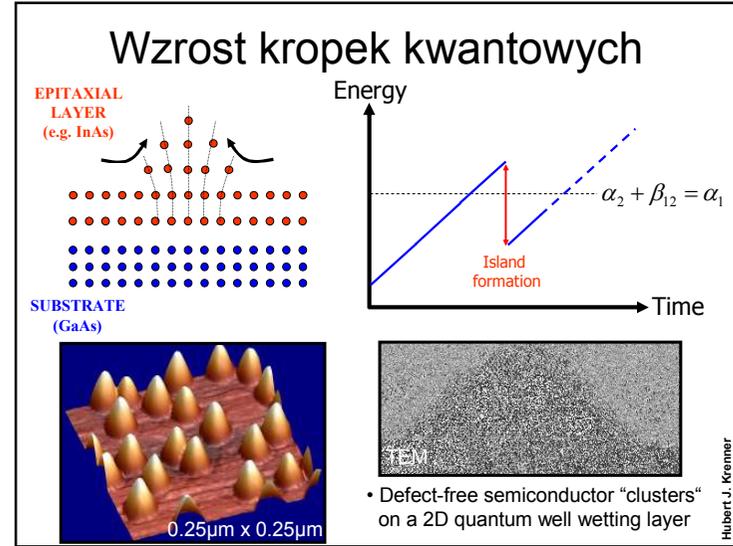
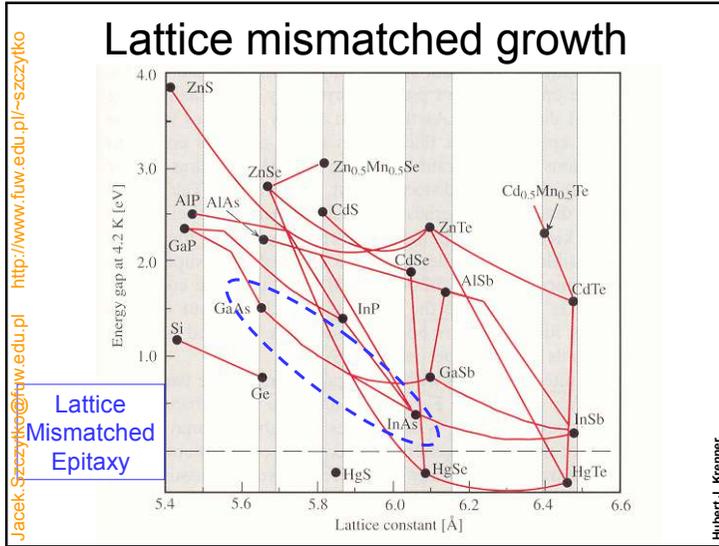
Distance ( $\mu\text{m}$ )

Height (nm)

Wasserman *et al.*, APL **85**, 5352 (2004)

Hubert J. Krenner

**Hubert J. Krenner**  
Walter Schottky Institut and Physik Department E24, TU München



**Doświadczenie**

Single mode fiber - mode field diameter  
Collection (600  $\mu\text{m}$ ) 5.5  $\mu\text{m}$

$T=300\text{K}$   
Minimum step  $\sim 50\text{ nm}$   
Maximum step  $\sim 1\ \mu\text{m}$   
 $T=4.2\text{K}$   
Minimum step  $\sim 5\text{ nm}$   
Maximum step  $\sim 100\text{ nm}$

0.2-1  $\mu\text{m}$

300  $\mu\text{m}$

A.Babinski, et al. Physica E 26 (2005) 190  
FUW Hoża 69

<http://www.fuw.edu.pl/~szczzytko>

## Access to individual QDs

Emission spectrum

CdTe/ZnTe

Intensity [a. u.]

Photon energy (eV)

sample

7mm

laser beam

prof. J. A. Gaj  
prof. M. Nawrocki  
dr hab. A. Golnik  
dr P. Kossacki

mgr W. Maślana  
mgr J. Suffczyński  
mgr K. Kowalik  
mgr W. Pacuski

mgr A. Trajnerowicz  
mgr B. Piechal  
M. Goryca  
T. Kazimierzuk

FUW  
Hoża 69

## GaN/AlGaIn QD's

Energy: 3.22eV

Energy: 3.33eV

Energy: 3.38eV

Energy: 3.34eV

$\mu\text{PL}$  - Barbara Chwalisz et al.

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## GaN/AlGaIn QD's

c575

PL Intensity (arb. units)

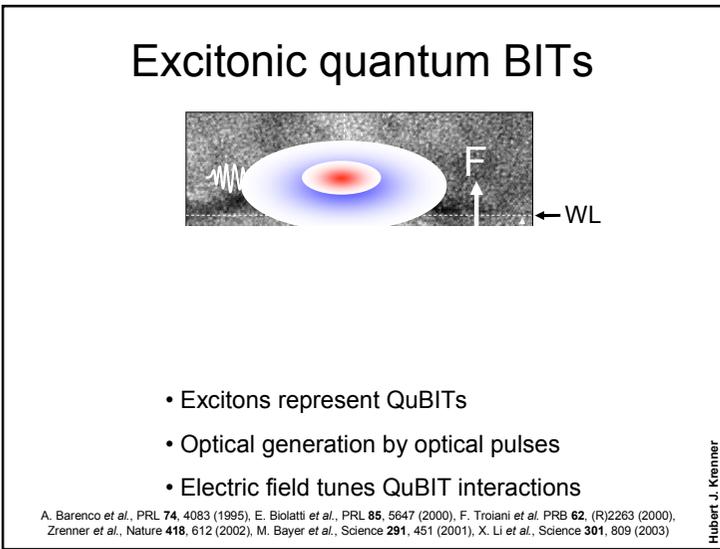
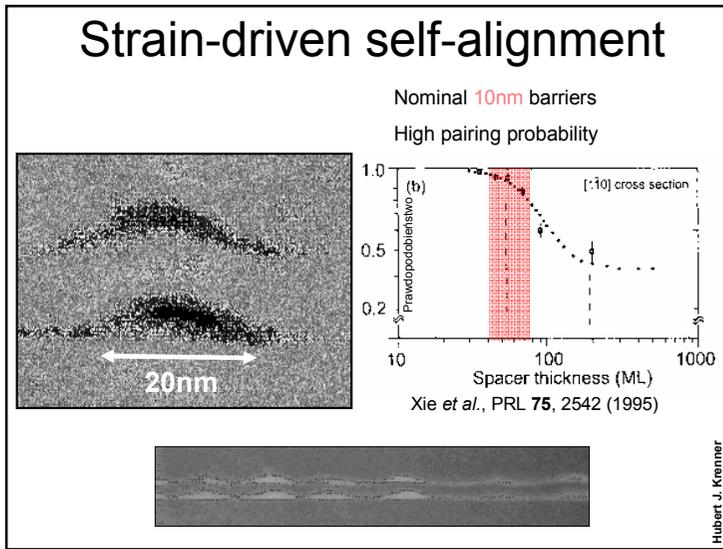
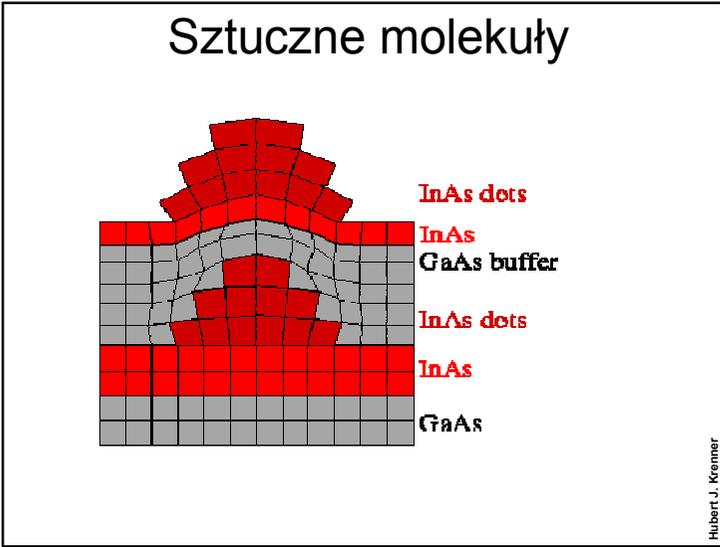
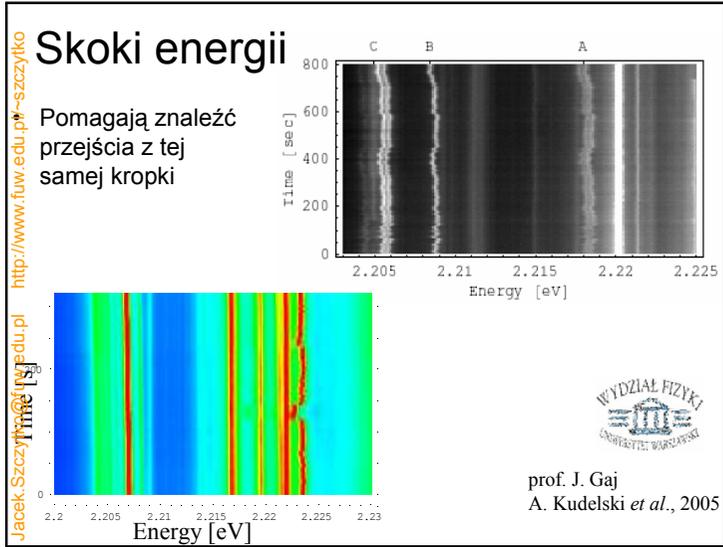
Energy (eV)

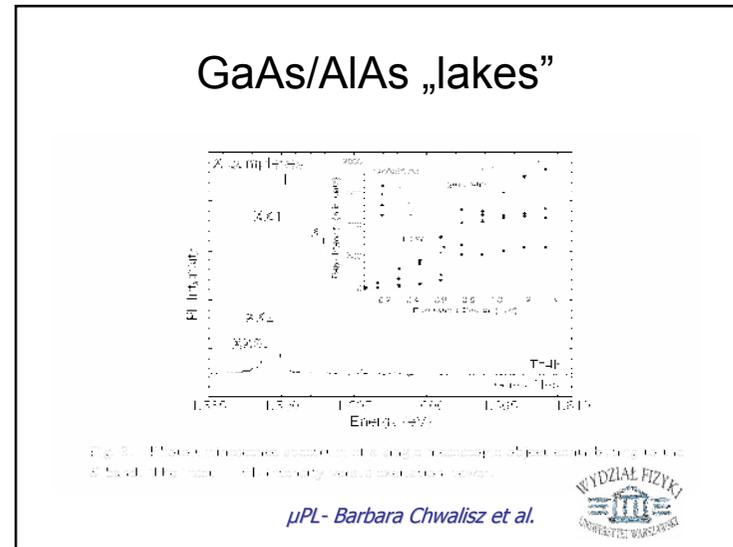
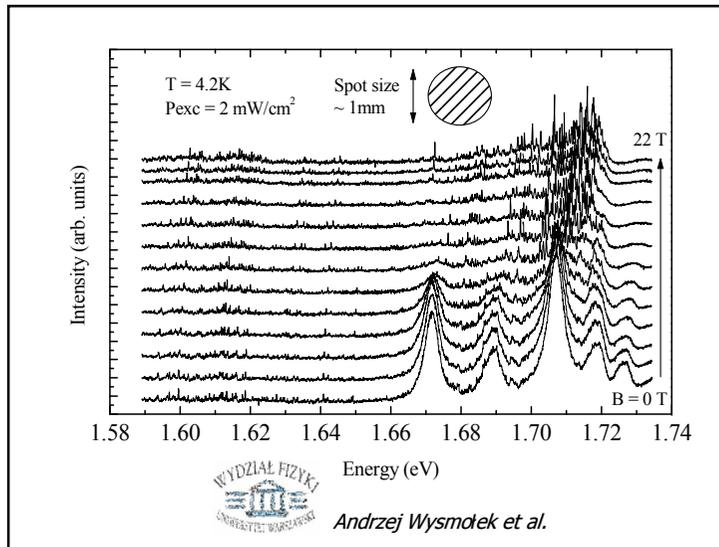
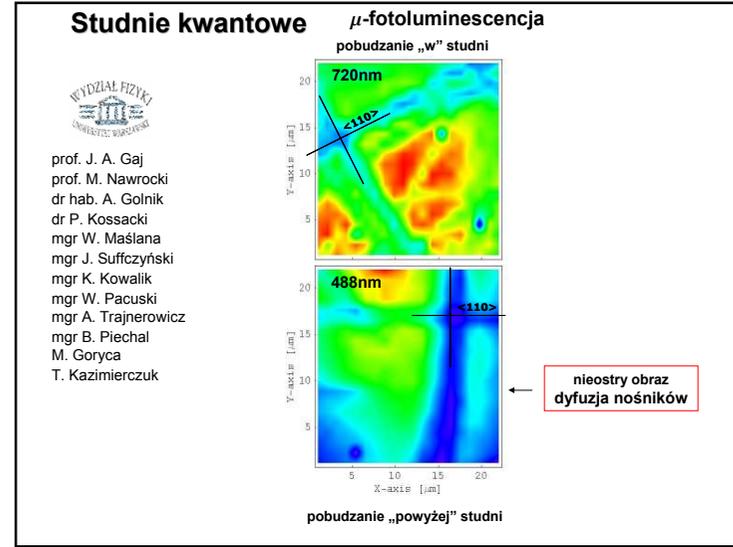
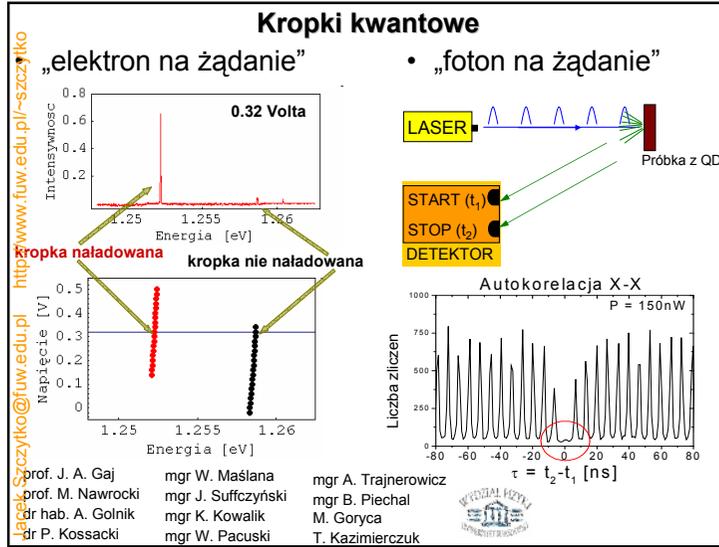
$\Delta E = 7\text{meV}$

time 100 X 16s

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$\mu\text{PL}$  - Katarzyna Surowiecka et al.





## Kropki kwantowe + bio

T2-MP EVITAGS  
Non-heavy Metal - InP Based, Water Stabilized Quantum Dots

Functional Liquid Coating

Ternary III-V EviDot    InGaP Core    Molecular Plate™ Shell    T2-MP EviTag - InGaP/ZnS with Lipid

Cd (CADMIUM)    Se (SELENIUM)    Zn (ZINC)    S (SULFUR)

CdSe Core EviDot    CdSe/ZnS Core-Shell EviDot

A PbSe Quantum Dot as seen through a transmission electron microscope (TEM).  
20 nm

Jacek.Szczytko@fuw.edu.pl    http://www.fuw.edu.pl/~szczytko

http://www.evidenttech.com/

## Kropki kwantowe + bio

Double duty. Green quantum dots cling to mitochondria in the cytoplasm; orange ones label proteins in the same cells' nuclei.

Science, Vol 300, Issue 5616, 80-81, 4 April 2003

## Kropki kwantowe + bio

Bull's-eye. Red quantum dots injected into a live mouse mark the location of a tumor.

Science, Vol 300, Issue 5616, 80-81, 4 April 2003

## Nanotechnologie

Total spend on nanotechnology

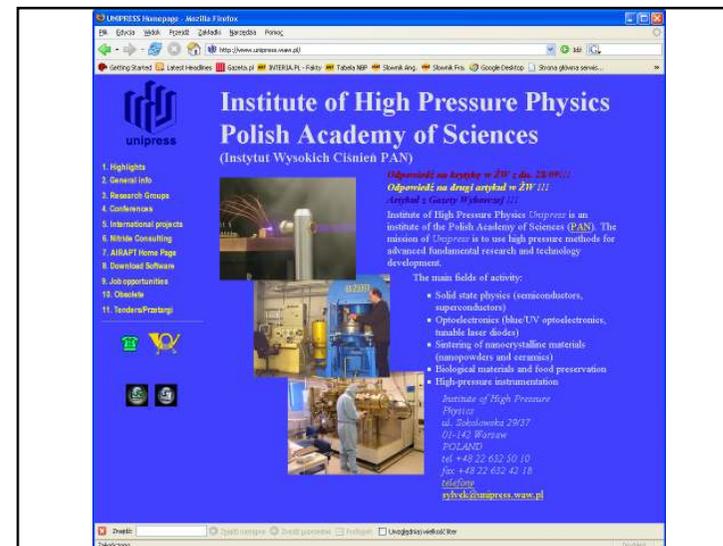
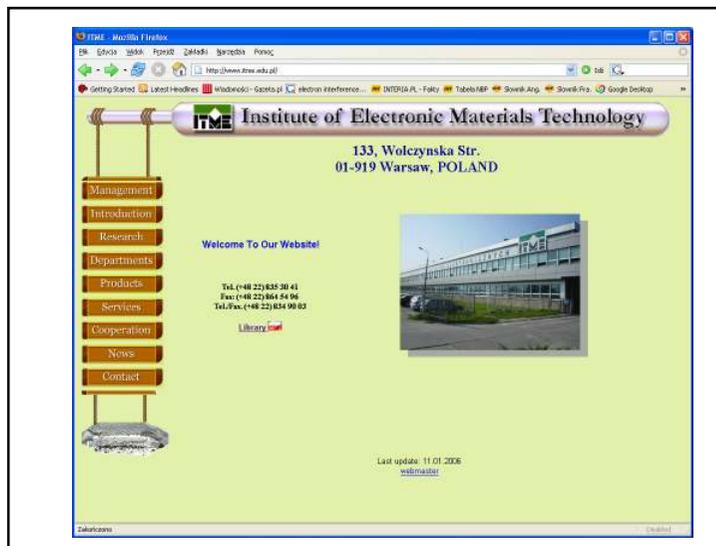
Type of company or institution

Type of company or institution	Percentage
Start Up	10%
SME	15%
Large Company or Multinational	31%
Government	8%
Private Research Institute	18%
Academic Institution	18%

Towards a European Strategy for Nanotechnology

COMMUNICATION FROM THE COMMISSION

Jacek.Szczytko@fuw.edu.pl http://www.fuw.edu.pl/~szczytko



TopGaN - a better lasers company - Mozilla Firefox

http://www.topgan.pl/~szcztytko

Medium-to high power laser diodes and laser modules for your advanced application in blue-violet-UV spectral range. World unique Plasma Assisted Molecular Beam Epitaxy (PAMBE) method used for nitride laser structures manufacturing.

TopGaN is a new manufacturer of blue/violet/UV laser diodes constructed using unique and proprietary technology developed in Unipress, the Institute of Basic Academy of Sciences. The main current products are: high power pulse current laser diodes and laser modules for applications in spectroscopy, medicine, pollution detection and many others. Our pulse current devices emit up to 1 W of optical power (peak value). We also introduce high power CW operated laser diodes with output power in the range of 100-300 mW. Additionally, we offer:
 

- reaction made optical wafers of AlGaInN for optoelectronics and electronics
- free standing GaN substrates and seeds
- high-pressure treatment of materials.

New offer of TopGaN:  
 0.5 W pulse current operated laser diodes.  
 100 mW CW laser modules.  
 One inch wafers of high quality, free standing GaN crystals made by HVPE.

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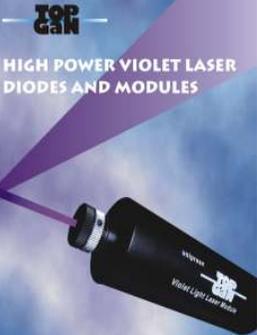



TOP GAN

OUR LASER MODULES FEATURE CUSTOMER-TAILORED DEVICE PARAMETERS \* WATT RANGE OPTICAL POWER (PULSE)

HIGH POWER VIOLET LASER DIODES AND MODULES

OUR COMPANY USES PROPRIETARY TECHNOLOGY OF BULK GAN SUBSTRATE CRYSTALS DEVELOPED BY UNIPRESS (POLAND)





**Niebieskie lasery są ciągle bardzo drogie – 2000 USD/sztukę !**

**4.1 Manufacturers of Laser Diode Chips**

- 4.1.1 Cree, USA
- 4.1.2 Matsushita, Japan
- 4.1.3 NEC, Japan
- 4.1.4 Nichia, Japan
- 4.1.5 Osram Opto Semiconductors, Germany
- 4.1.6 Pioneer, Japan
- 4.1.7 Rohm, Japan
- 4.1.8 Samsung, Korea
- 4.1.9 Sanyo Electric, Japan
- 4.1.10 Sharp, Japan
- 4.1.11 Sony, Japan
- 4.1.12 TopGaN, Poland
- 4.1.13 Toshiba, Japan
- 4.1.14 Toyoda Gosei, Japan

Strategy Analytics

March 2004

http://www.strategyanalytics.com/

Czesław Skierbiszewski UNIPRESS

AMMONO - Mozilla Firefox

http://www.ammono.com.pl/

Panoramic Color Shows

Great discoveries and improvements invariably involve the cooperation of many minds. Alexander Graham Bell

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AMMONO

AMMONO - official internet site - www.ammono.com.pl - contact - info@ammono.com.pl

Przesyłanie danych z www.ammono.com...

Jacek.Szczytko@fuw.edu.pl http://www.fuw.edu.pl/~szczytko



## Podziękowania

Zakład Fizyki Ciała Stałego <http://www.fuw.edu.pl/~zfcsl/>  
prof. dr hab. M. Baj



Struktury Kwantowe GaAs/AIAs

mgr B. Chwalisz	Prof. M. Baj
dr A. Wyszomolek	dr hab. D. Wasik
dr M. Potemski (GHMFL)	dr J. Siwicki
prof. R. Stepniowski	

Spektroskopia ultraszybką

prof. J. Gaj,	prof. R. Stepniowski
prof. M. Nawrocki,	mgr K. Pakula
dr hab. A. Golnik,	mgr R. Bożek
M. Goryca,	mgr K. Surowiecka
T. Kazmierczuk,	dr A. Wyszomolek
dr P. Kossacki,	mgr B. Chwalisz
K. Kowalik,	prof. J. Baranowski
W. Maślana,	dr K. Kossacki
W. Pacuski,	dr K. Korona
B. Piechal,	dr hab. A. Golnik
J. Suffczyński,	
A. Trajnerowicz	



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dr Jerzy Łusakowski,  
dr Krzysztof Karpierz,  
mgr Maciej Sakowicz,  
prof. dr hab. Marian Grynbeg

Spintronika

prof. dr hab. Maria Kamińska  
prof. dr hab. Andrzej Twardowski  
dr Jacek Gosk  
dr Jacek Szczytko,  
mgr Konrad Działkowski,  
mgr Marcin Zajac

W następnym tygodniu:

## Nanotechnologia III i IV



1. Miniaturyzujemy III.
  - a. Nanorurki
    - i. Węgiel i nie tylko
    - ii. Pokręcone zasady
2. Nanomaszyny

